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INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

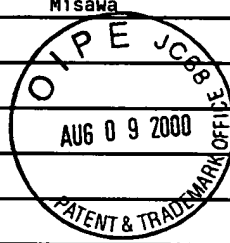
Applicant: Shunpei YAMAZAKI et al.

Filing Date: 11/23/98

Group: 2874

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| Examiner Initial | Patent Number | Issue Date | Patentee | Class | Subclass | Filing Date (if approp.) |
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Examiner

Date Considered

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